TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# T C 7 M H 5 7 3 F K

#### Octal D-Type Latch with 3-State Output

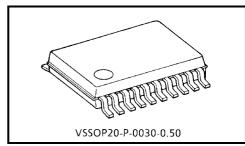
The TC7MH573FK is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate  $\rm C^2MOS$  technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

This 8 bit D-type latch is controlled by a latch enable input (LE) and a output enable input ( $\overline{OE}$ ).

When the  $\overline{OE}$  input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 7 V can be applied



Weight: 0.03 g (typ.)

to the input pins without regard to the supply voltage. This device can be used to interface 5~V to 3~V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

#### **Features**

- High speed:  $t_{pd} = 4.5 \text{ ns (typ.) (VCC} = 5 \text{ V)}$
- Low power dissipation:  $ICC = 4 \mu A \text{ (max) (Ta} = 25^{\circ}C)$
- High noise immunity: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays:  $t_pLH \approx t_pHL$
- Wide operating voltage range: VCC (opr) = 2~5.5 V
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with 74ALS573

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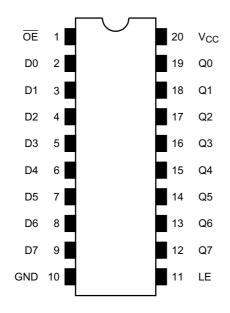
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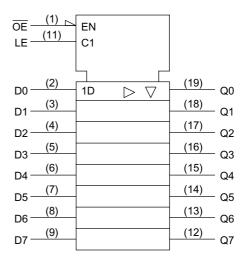
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### Pin Assignment (top view)



### **IEC Logic Symbol**



#### **Truth Table**

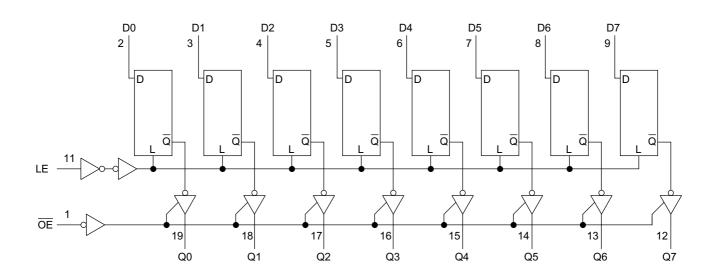
	Inputs	Outputs	
ŌĒ	LE	D	Outputs
Н	Х	X	Z
L	L	Х	Q <sub>n</sub>
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

 $Q_n$ : Q outputs are latched at the time when the LE input is taken to a low logic level.

### **System Diagram**





## **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	I <sub>OUT</sub>	±25	mA
DC V <sub>CC</sub> /ground current	I <sub>CC</sub>	±75	mA
Power dissipation	P <sub>D</sub>	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC}=3.3\pm0.3 \ V)$	ns/V
input rise and rail time	αί/αν	$0\sim20 \ (V_{CC}=5\pm0.5 \ V)$	115/ V



### **Electrical Characteristics**

### **DC Characteristics**

Characteristics		Symbol Test Condition		Condition		Ta = 25°C			Ta = -40~85°C		Unit
Cilarac	rensuos	Symbol			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
					2.0	1.50	_	_	1.50	_	
Input voltage	High level	$V_{IH}$		_		V <sub>CC</sub> ×0.7	_	_	V <sub>CC</sub> × 0.7	_	V
input voitage					2.0	_	_	0.50	_	0.50	V
	Low level	$V_{IL}$		_	3.0~5.5	_	_	V <sub>CC</sub> × 0.3	_	V <sub>CC</sub> ×0.3	
				$I_{OH} = -50 \mu A$	2.0	1.9	2.0		1.9		
					3.0	2.9	3.0		2.9	_	V
	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		4.5	4.4	4.5		4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
voltage					2.0	_	0	0.1	_	0.1	V
				$V_{IH}$ $I_{OL} = 50 \mu A$	3.0		0	0.1	_	0.1	
	Low level	$V_{OL}$	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		4.5	_	0	0.1	—	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0			0.36		0.44	
			I <sub>OL</sub> = 8 mA		4.5	_	—	0.36	—	0.44	
3-state output	off-state current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.25	_	±2.50	μА
Input leakage	current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5		_	±0.1	_	±1.0	μΑ
Quiescent sup	ply current	Icc	$V_{IN} = V_{CC}$	$V_{IN} = V_{CC}$ or GND				4.0		40.0	μΑ

## Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	mbol Test Condition		Ta = 25°C		Ta = -40~85°C	Unit
	Symbol	rest Condition	V <sub>CC</sub> (V)	Тур.	Limit	Limit	Offic
Minimum pulse width	<b>t</b>		$3.3\pm0.3$	_	5.0	5.0	no
(LE)	tw (H)	_	$5.0\pm0.5$	_	5.0	5.0	ns
Minimum set-up time			$3.3 \pm 0.3$	_	3.5	3.5	
	t <sub>s</sub>	_	$5.0\pm0.5$	_	3.5	3.5	ns
Minimum hold time	4.		$3.3 \pm 0.3$	_	1.5	1.5	no
	t <sub>h</sub>	_	$5.0 \pm 0.5$	_	1.5	1.5	ns



### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	7.6	11.9	1.0	14.0	
Propagation delay time	t <sub>pLH</sub>		3.3 ± 0.3	50	_	10.1	15.4	1.0	17.5	
(LE-Q)	t <sub>pHL</sub>	_	5.0 ± 0.5	15	_	5.0	7.7	1.0	9.0	ns
			3.0 ± 0.5	50	_	6.5	9.7	1.0	11.0	
			3.3 ± 0.3	15	_	7.0	11.0	1.0	13.0	
Propagation delay time	t <sub>pLH</sub>		3.3 ± 0.3	50	_	9.5	14.5	1.0	16.5	ns
(D-Q)	t <sub>pHL</sub>	_	5.0 ± 0.5	15	_	4.5	6.8	1.0	8.0	
			5.0 ± 0.5	50	_	6.0	8.8	1.0	10.0	
	t <sub>pZL</sub> t <sub>pZH</sub>	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15	_	7.3	11.5	1.0	13.5	- ns
2 state suitaut anable time				50	_	9.8	15.0	1.0	17.0	
3-state output enable time			5.0 ± 0.5	15	_	5.2	7.7	1.0	9.0	
				50	_	6.7	9.7	1.0	11.0	
3-state output disable time	t <sub>pLZ</sub>	$R_L = 1 \text{ k}\Omega$	$3.3 \pm 0.3$	50	_	10.7	14.5	1.0	16.5	ns
3-state output disable time	tpHZ		$5.0 \pm 0.5$	50	_	6.7	9.7	1.0	11.0	115
Output to output skew	t <sub>osLH</sub>	(Note1)	$3.3 \pm 0.3$	50	_	_	1.5	_	1.5	ns
Output to output skew	t <sub>osHL</sub>	(Note I)	$5.0 \pm 0.5$	50	_	_	1.0	_	1.0	115
Input capacitance	C <sub>IN</sub>		_		_	4	10	_	10	pF
Output capacitance	C <sub>OUT</sub>	-	_			6		_	_	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note2)	_	29	_	_	_	pF

Note1: This parameter is guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \ t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|$ 

Note2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per latch)$ 

And the total C<sub>PD</sub> when n pcs of latch operate can be gained by the following equation:

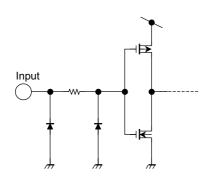
C<sub>PD</sub> (total) = 21 + 8 · n



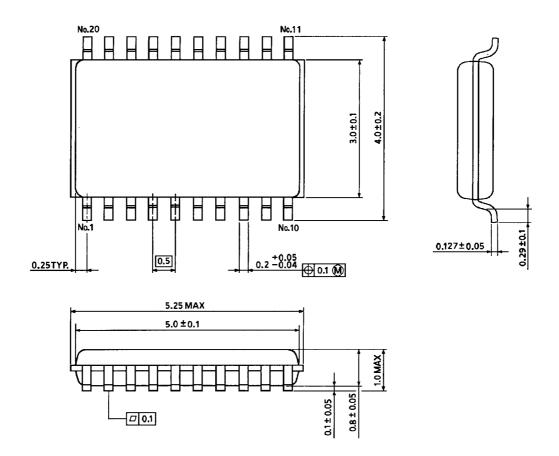
## Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Gridiacieristics	Syllibol	rest Condition	V <sub>CC</sub> (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	0.8	1.0	V
Quiet output minimum dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.8	-1.0	V
Minimum high level dynamic input voltage $V_{\text{IH}}$	V <sub>IHD</sub>	C <sub>L</sub> = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage $V_{\text{IL}}$	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	1.5	V

### **Input Equivalent Circuit**



### **Package Dimensions**



Weight: 0.03 g (typ.)